

isc Silicon NPN Power Transistor

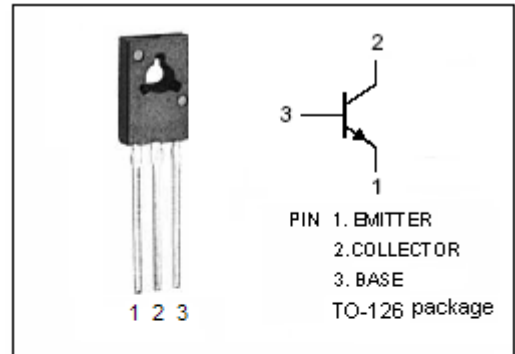
2SC2481

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V(\text{Min})$
- High Current Capability
- High Collector Power Dissipation
- Complement to Type 2SA1021

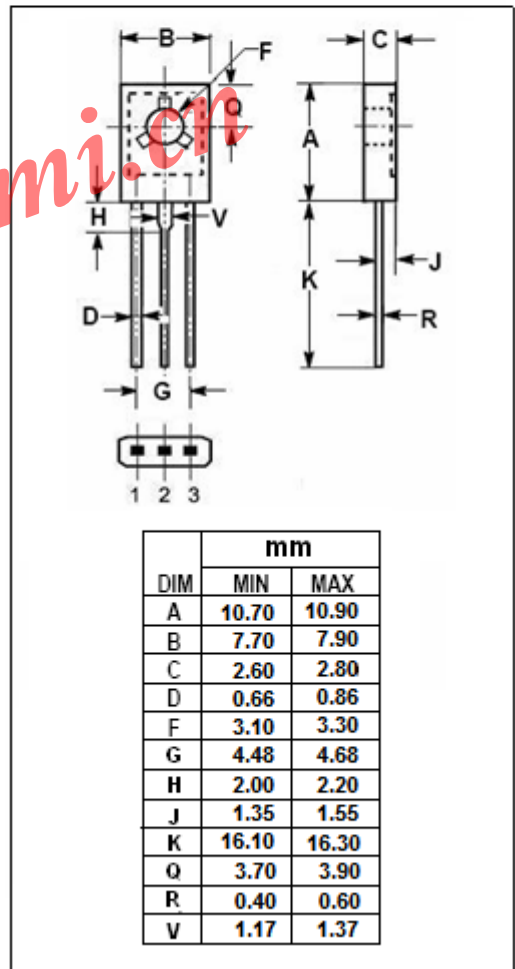
APPLICATIONS

- Color TV vertical deflection output applications.
- Color TV class B sound output applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1.5	A
I_B	Base Current-Continuous	1.0	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.2	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC2481****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.5\text{A}; I_B=50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=5\text{mA}; V_{CE}=5\text{V}$			0.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=150\text{V}; I_E=0$			1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			1.0	μA
h_{FE}	DC Current Gain	$I_C=0.2\text{A}; V_{CE}=5\text{V}$	60		320	
f_T	Current-Gain—Bandwidth Product	$I_C=0.2\text{A}; V_{CE}=5\text{V}$	20	100		MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		13		pF

◆ **h_{FE} Classifications**

R	O	Y
60-120	100-200	160-320